

ELECTROLYTE FOR FORMING ANODIC OXIDE FILM, METHOD OF FORMING
ANODIC OXIDE FILM, AND ANODIC OXIDE FILM AND MEMBER FOR
SEMICONDUCTOR DEVICE MANUFACTURED THEREBY

ABSTRACT

Proposed are an electrolyte for forming an anodic oxide film, the electrolyte including citric acid and an additive, wherein the citric acid accounts for 3.0 wt% or more and 6.0 wt% or less based on 100 wt% of the electrolyte, the additive includes one or more selected from among tartaric acid, sulfuric acid, and sodium acetate, and the additive accounts for 0.5 wt% or more and 4.0 wt% or less based on 100 wt% of the electrolyte, a method of forming an anodic oxide film using the electrolyte, and an anodic oxide film and a member for a semiconductor device manufactured thereby.

[Fig. 3]